N-Channel Enhancement Mode Power MOSFET

Description

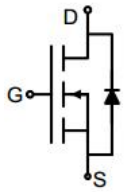
The GT110N06S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

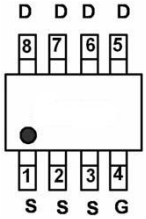
- V_{DS} 60V
- I_D (at V_{GS} = 10V) 14A
- $R_{DS(ON)}$ (at V_{GS} = 10V) < 11mΩ
- $R_{DS(ON)}$ (at V_{GS} = 4.5V) < 14mΩ
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



pin assignment

SOP-8

Ordering Information

Device	Package	Marking	Packaging
GT110N06S	SOP-8	GT110N06	4000pcs/Reel

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current	I_D	14	A
Pulsed Drain Current (note1)	I_{DM}	56	A
Gate-Source Voltage	V_{GS}	±20	V
Power Dissipation	P_D	3	W
Single pulse avalanche energy （note2）	E_{AS}	49	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	ºC

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	40	ºC/W

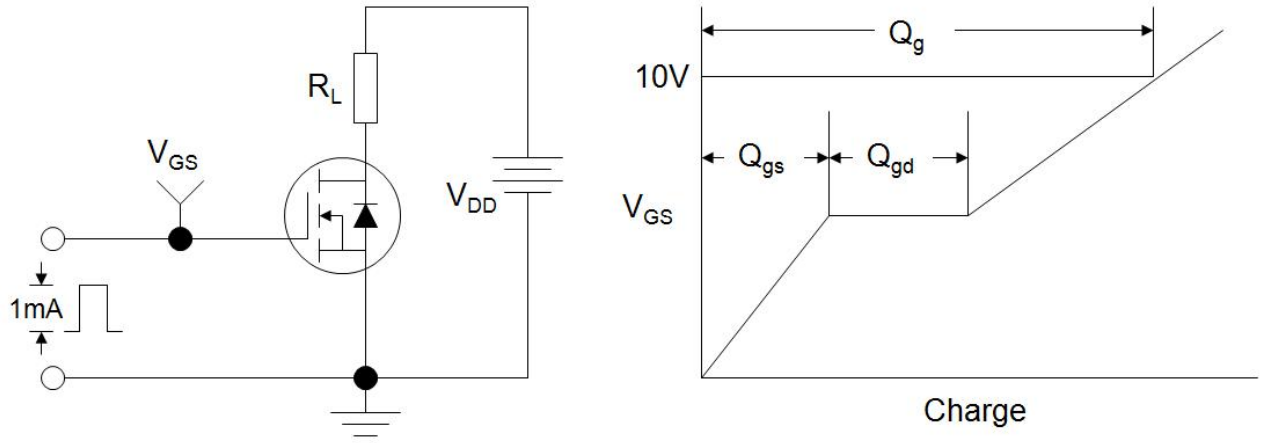
Specifications T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	60	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60V, V_{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1	1.6	2.4	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 8A	--	8.5	11	mΩ
		V_{GS} = 4.5V, I_D = 8A	--	10	14	
Forward Transconductance	g_{FS}	V_{GS} = 5V, I_D = 8 A	--	25	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 30V, f = 1.0MHz	--	1475	--	pF
Output Capacitance	C_{oss}		--	365	--	
Reverse Transfer Capacitance	C_{rss}		--	9	--	
Total Gate Charge	Q_g	V_{DD} = 30V, I_D = 8A, V_{GS} = 10V	--	24	--	nC
Gate-Source Charge	Q_{gs}		--	7	--	
Gate-Drain Charge	Q_{gd}		--	2.5	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 30V, I_D = 8A, R_G = 10Ω	--	6	--	ns
Turn-on Rise Time	t_r		--	3	--	
Turn-off Delay Time	$t_{d(off)}$		--	25	--	
Turn-off Fall Time	t_f		--	3	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	14	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 8A, V_{GS} = 0V	--	--	1.2	V
Reverse Recovery Charge	Qrr	I_F = 8A, V_{GS} = 0V di/dt=500A/us	--	60	--	nC
Reverse Recovery Time	Trr		--	19	--	ns

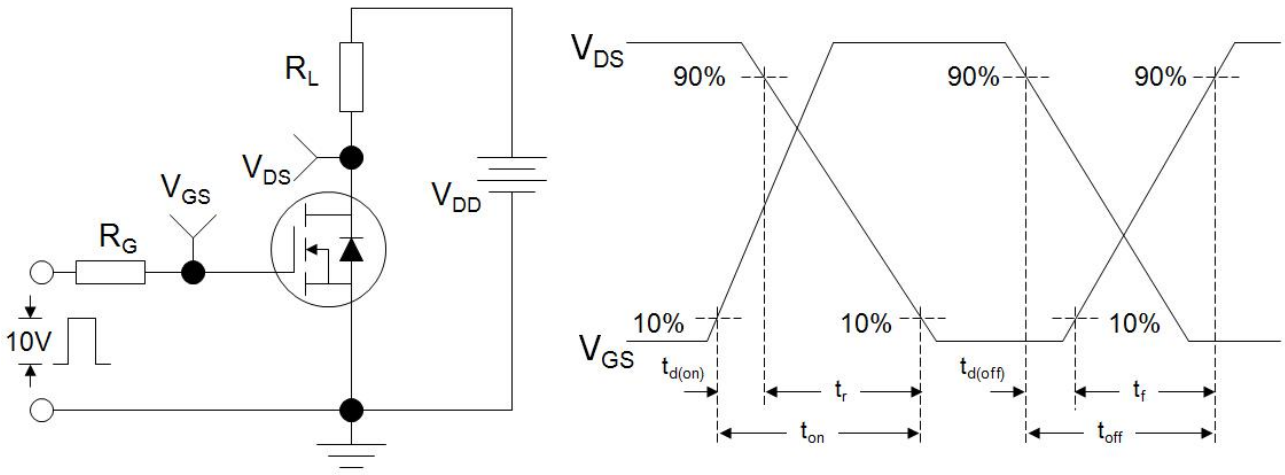
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : Tj=25℃ ,VDD=50V,VGS=10V,L=0.5mH,Rg=25Ω
3. Identical low side and high side switch with identical R_G

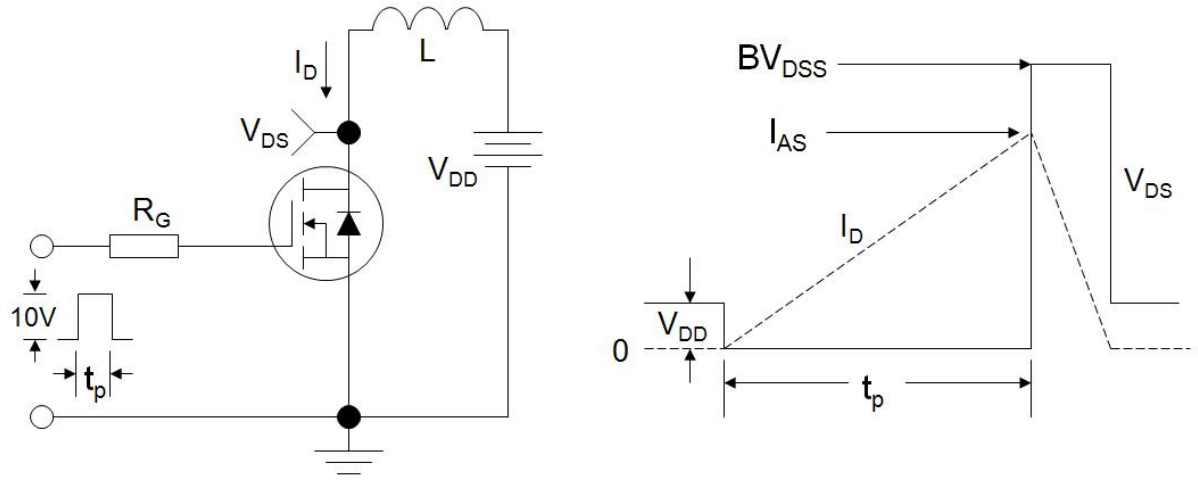
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

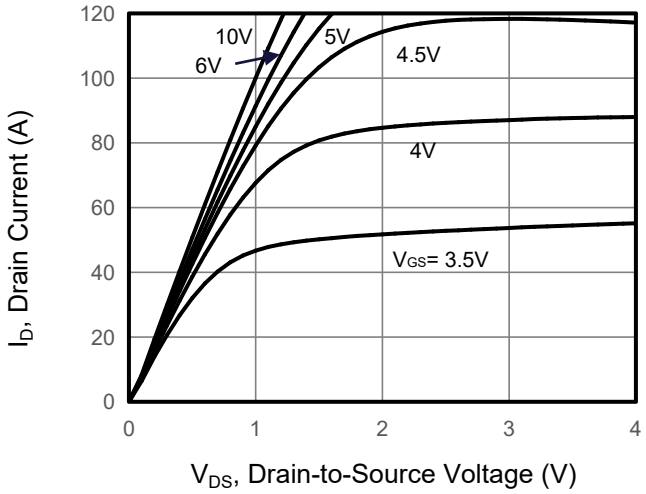


Figure 2. Transfer Characteristics

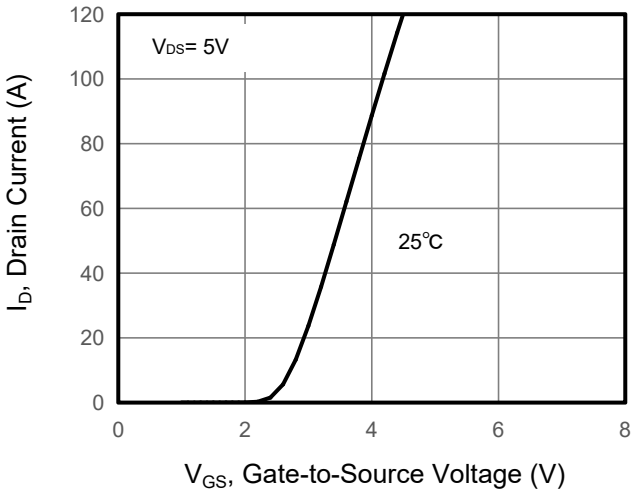


Figure 3. Drain Source On Resistance

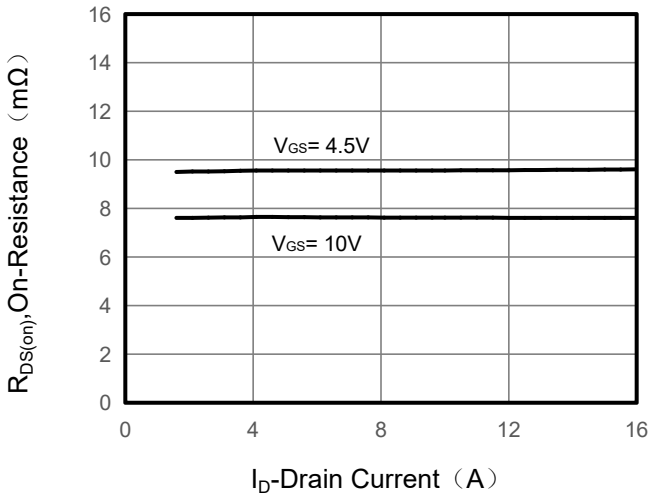


Figure 4. Gate Charge

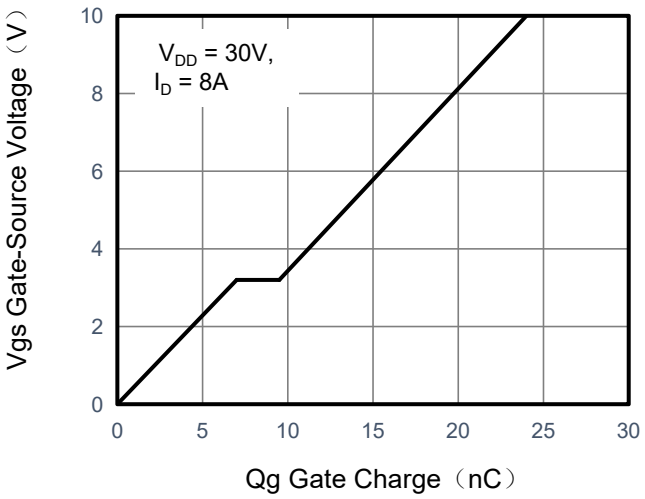


Figure 5. Capacitance

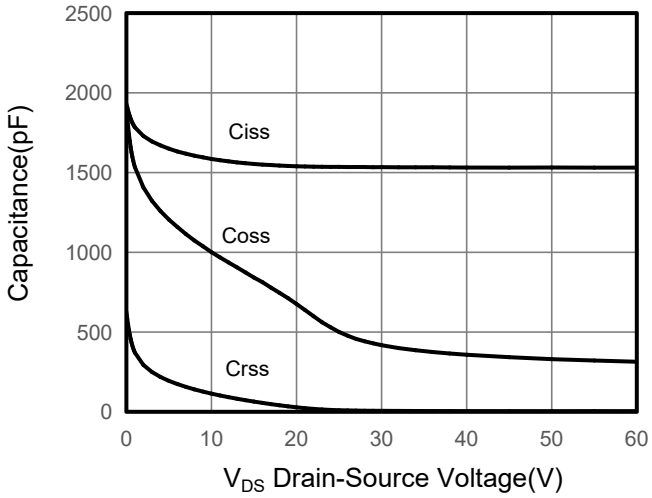
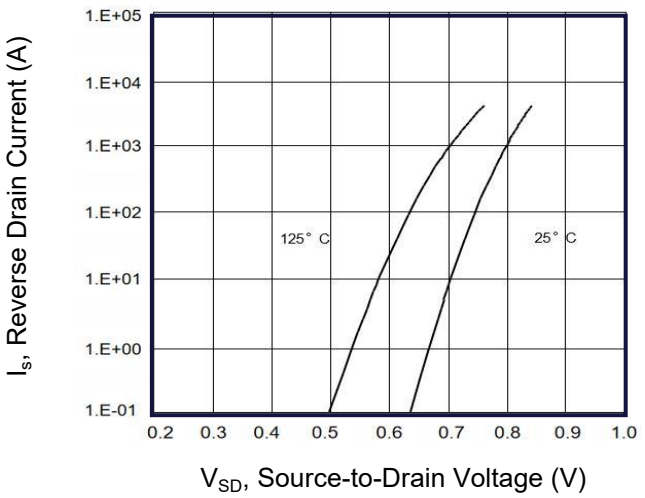


Figure 6. Source-Drain Diode Forward



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Drain-Source On-Resistance

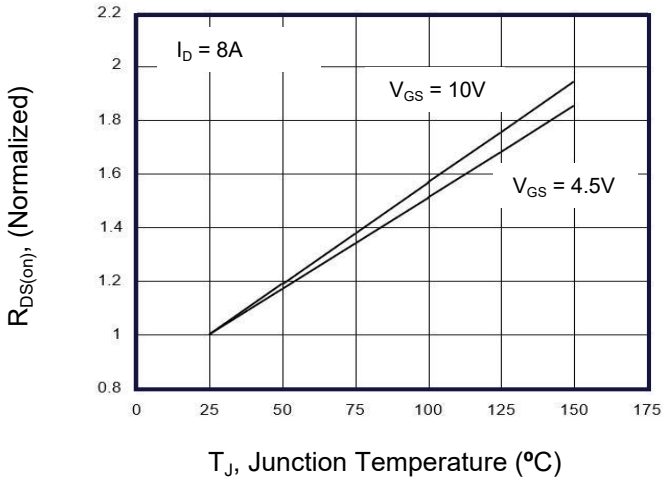


Figure 8. Safe Operation Area

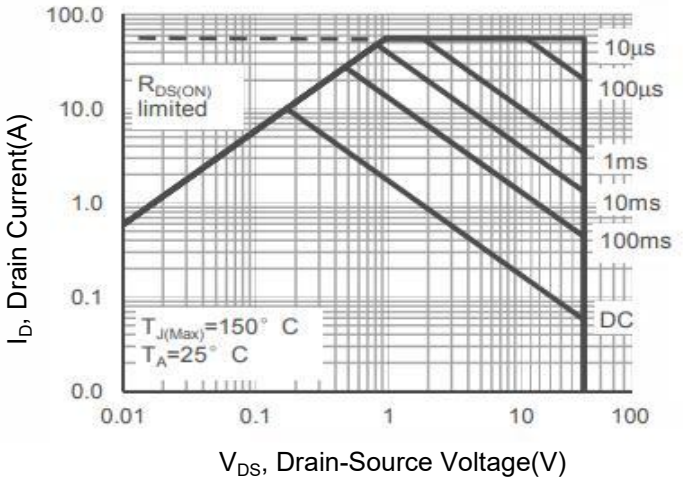
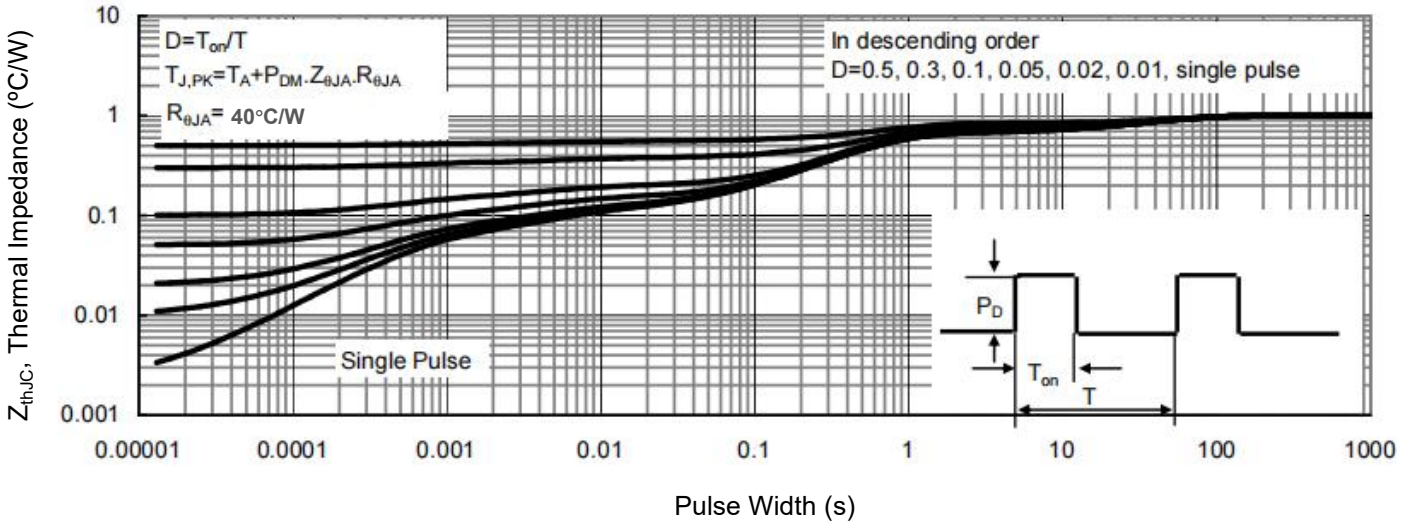
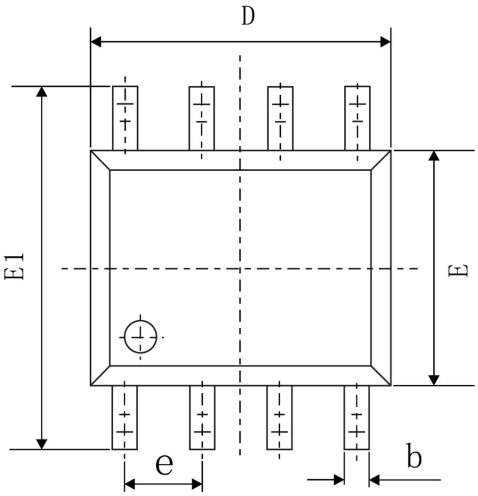


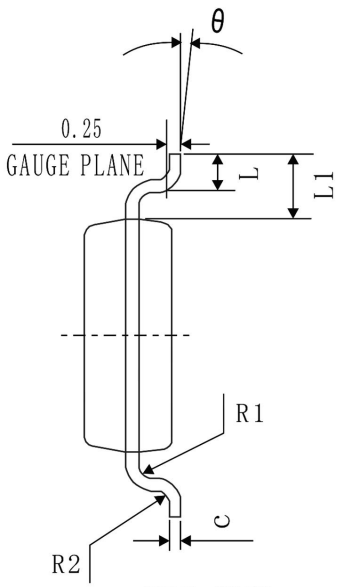
Figure 9. Normalized Maximum Transient Thermal Impedance



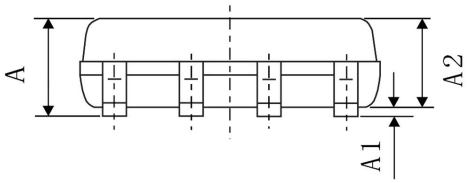
SOP-8 Package Information



TOP VIEW



SIDE VIEW



SIDE VIEW

COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	1.40	1.60	1.80
A1	0.05	0.15	0.25
A2	1.35	1.45	1.55
b	0.30	0.40	0.50
c	0.153	0.203	0.253
D	4.80	4.90	5.00
E	3.80	3.90	4.00
E1	5.80	6.00	6.20
L	0.45	0.70	1.00
θ	2°	4°	6°
L1	1.04 REF		
e	1.27 BSC		
R1	0.07 TYP		
R2	0.07 TYP		